LISTING OF THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

1. (Cancelled)

2. (Currently Amended) A method for forming a reflective reflector pattern comprising:

forming a micropattern using an organometallic-containing compound through a photoreaction or thermal energy through the following steps:

(a) coating the organometallic-containing compound on a substrate to form a thin film,

(b) exposing the thin film to light through a mask to decompose the organometallic-containing compound at exposed area and to induce a difference in solubility between the exposed and unexposed areas and developing the thin film to remove the organometallic-containing compound of the unexposed area, and

(c) reducing or oxidizing the exposed area to form a metal pattern or metal oxide pattern; and

growing crystal, using the pattern as a nucleus for growing crystal, by an electro or electroless Ag plating process.

3. (Currently Amended) A method for forming a reflective reflector pattern comprising:

forming a micropattern using an organometallic-containing compound through a photoreaction or thermal energy through the following steps:

(a) forming a pattern using the organometallic-containing compound through soft

lithography or ink jet printing, and

(b) heating the pattern to decompose the organometallic-containing compound; and

growing crystal, using the pattern as a nucleus for growing crystal, by an electro or electroless Ag plating process.

4. (Original) The method according to claim 3, wherein the soft lithography is microcontact printing or micromolding in capillaries (MIMIC).

5. (Currently amended) The method according to claim 2 ~~or 3~~, wherein the organometallic-containing compound is represented by the following formula 1:

$M_mL_2X_p$ (1)

wherein M is a metal; L is a ligand; X is a monovalent to trivalent anion; m is an interger from 1 to 10, and when m is 2 or more, each M may be different from the other; n is an integer from 0 to 60, and when n is 2 or more, each L may be different from the other; p is an integer from 0 to 60, and when p is 2 or more, each X may be different from the other; L may act as a ligand bonding two metals when two or more metals are used; and n and p are not simultaneously 0.

6. (Previously Presented) The method according to claim 5, wherein M is a late transition metal (IX~XII) selected from the group consisting of Co, Ni, Pd, Pt, Cu, Ag, Au, An and Ce, or A1.

7. (Previously Presented) The method according to claim 5, wherein L is a ligand selected from the group consisting of acetylacetonates, acetates, ß-ketoiminates, ß-diiminates, ß-ketoesters, dialkyldithiocarbamates, carboxylates, oxalate, alkoxy ligands, pyridines, amines, diamines, arsines, diarsines, phosphines, diphosphines, arenas, carbonyl, imidazolylidene, ethylene, acetylene, aquo, thiocarbonyl, thioether and a derivative thereof.

8. (Previously Presented) The method according to claim 5, wherein X is an anion selected from the group consisting of halogen, hydroxy, cyanide (CN_3^-), nitrite (NO_2^-), nitrate (NO^-), nitrosyl (NO^-), azide (N_4^-), thiocyanate (NCS_3), isothiocyanate (SCN_4^-), tetraalkylborate (BR_4^-, R = methyl, ethyl or phenyl group), tetrahaloborate (BX_4^-, X = F, Br), hexafluorophosphate (PF_6^-), triflate ($CF_3SO_3^-$), tosylate (Ts^-), sulfate (SO_4^{2-}), and carbonate (CO_3^{2-}).

9. (Previously Presented) The method according to claim 6, wherein the organometallic-containing compound is a silver compound.

10. (Cancelled)

11. (Cancelled)

12. (Previously Presented) The method according to claim 5, wherein M is at least one transition metal, lanthanide or A1.

13. (New) The method according to claim 3, wherein the organometallic-containing compound is represented by the following formula 1:

$M_mL_2X_p$ (1)

wherein M is a metal; L is a ligand; X is a monovalent to trivalent anion; m is an interger from 1 to 10, and when m is 2 or more, each M may be different from the other; n is an integer from 0 to 60, and when n is 2 or more, each L may be different from the other; p is an integer from 0 to 60, and when p is 2 or more, each X may be different from the other; L may act as a ligand bonding two metals when two or more metals are used; and n and p are not simultaneously 0.